

**REMARKS**

Claim 1 had been amended. New claims 15-16 have been added. No claims have been canceled. Accordingly, claims 1 and 15-19 are currently pending in the above-identified application.

**Priority**

Applicants appreciate the Examiner's acknowledgment of the claim for priority and receipt of the priority document in the parent application.

**Specification**

The title has been amended as required by the Examiner.

**35 U.S.C. §102**

Claim 1 stands rejected under 35 U.S.C. §102(b) as being anticipated by Watanabe (U.S. Patent No. 4,527,259). This rejection is traversed as follows.

The present invention is directed to a semiconductor integrated circuit having nonvolatile memory cells wherein each cell has one memory transistor including a gate insulating film with discreet traps. The semiconductor integrated circuit includes two switch transistors and two

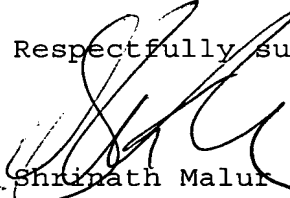
diffusion layers and the switch transistors are formed between the two diffusion layers. The memory transistor is formed between the two switch transistors. Each channel of the memory transistor and the two switch transistors are formed in a continuous portion between the two diffusion layers. Therefore, one bit of information can be written to both ends of the gate insulating film which have discreet traps due to source side injection. In addition to being able to accomplish this quickly, the area taken up by the memory cell is reduced.

On the other hand, Watanabe shows in Fig. 5 that an n-type drain region is formed between the channel of the insulated gate field effect transistor and the channel of the MNOS element 7. Therefore, the respective channels of the insulated gate field effect transistors and the MNOS element are isolated from each other by the n-type drain region 15 and the n-type source region 16. Therefore, the respective channels are not formed continuously between the n-type source region 14 and the n-type drain region 17. As such, it is submitted that the pending claims patentably define the present invention over the cited art.

**Conclusion**

In view of the foregoing amendments and remarks, Applicants contend that the above-identified application is now in condition for allowance. Accordingly, reconsideration and reexamination are respectfully requested.

Respectfully submitted,

  
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